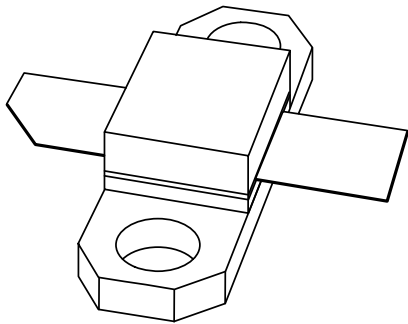


DATA SHEET



BLF1822-10 UHF power LDMOS transistor

Product specification
Supersedes data of 2002 Mar 12

2003 Feb 10

UHF power LDMOS transistor

BLF1822-10

FEATURES

- Typical 2-tone performance at a supply voltage of 26 V and I_{DQ} of 85 mA:
 - Output power = 10 W (PEP)
 - Gain = 18.5 dB at 900 MHz, 13.5 dB at 2200 MHz
 - Efficiency = 39% at 900 MHz, 34% at 2200 MHz
 - dim = -31 dBc at 900 MHz, -28 dBc at 2200 MHz
- Easy power control
- Excellent ruggedness
- High power gain
- Excellent thermal stability
- Designed for broadband operation (HF to 2200 MHz)
- No internal matching for broadband operation.

APPLICATIONS

- RF power amplifiers for GSM, EDGE, CDMA and W-CDMA base stations and multicarrier applications in the HF to 2200 MHz frequency range
- Broadcast drivers.

DESCRIPTION

10 W LDMOS power transistor for base station applications at frequencies from HF to 2200 MHz.

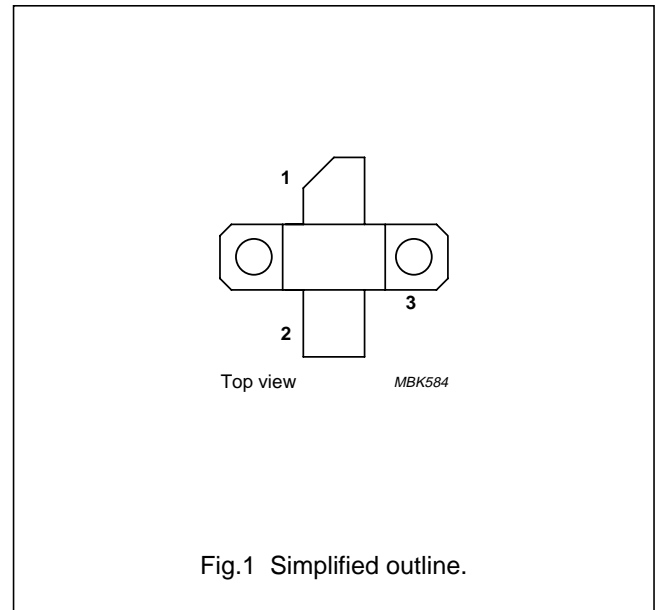
QUICK REFERENCE DATA

RF performance at $T_h = 25\text{ }^\circ\text{C}$ in a common source test circuit.

MODE OF OPERATION	f (MHz)	V_{DS} (V)	I_{DQ} (mA)	P_L (W)	G_p (dB)	η_D (%)	d_{im} (dBc)
CW, class-AB (2-tone)	$f_1 = 2200; f_2 = 2200.1$	26	85	10 (PEP)	>11; typ. 13.5	>30; typ. 34	≤ -26 ; typ. -28
	$f_1 = 960; f_2 = 960.1$	26	85	10 (PEP)	typ. 18.5	typ. 39	typ. -33

PINNING - SOT467C

PIN	DESCRIPTION
1	drain
2	gate
3	source, connected to flange



CAUTION

This product is supplied in anti-static packing to prevent damage caused by electrostatic discharge during transport and handling. For further information, refer to Philips specs.: SNW-EQ-608, SNW-FQ-302A and SNW-FQ-302B.

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V_{DS}	drain-source voltage	–	65	V
V_{GS}	gate-source voltage	–	± 15	V
I_D	drain current (DC)	–	2.2	A
T_{stg}	storage temperature	–65	+150	°C
T_j	junction temperature	–	200	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-mb}$	thermal resistance from junction to mounting base	$T_{mb} = 25\text{ °C}$; note 1	5	K/W
$R_{th\ mb-h}$	thermal resistance from mounting base to heatsink		0.5	K/W

Note

1. Thermal resistance is determined under RF operating conditions.

CHARACTERISTICS $T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0$; $I_D = 0.2\text{ mA}$	65	–	–	V
V_{GSth}	gate-source threshold voltage	$V_{DS} = 10\text{ V}$; $I_D = 20\text{ mA}$	4	–	5	V
I_{DSS}	drain-source leakage current	$V_{GS} = 0$; $V_{DS} = 26\text{ V}$	–	–	1.5	μA
I_{DSX}	on-state drain current	$V_{GS} = V_{GSth} + 9\text{ V}$; $V_{DS} = 10\text{ V}$	2.8	–	–	A
I_{GSS}	gate leakage current	$V_{GS} = \pm 15\text{ V}$; $V_{DS} = 0$	–	–	40	nA
g_{fs}	forward transconductance	$V_{DS} = 10\text{ V}$; $I_D = 0.75\text{ A}$	–	0.5	–	S
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10\text{ V}$; $I_D = 0.75\text{ A}$	–	1.2	–	Ω
C_{is}	input capacitance	$V_{GS} = 0$; $V_{DS} = 26\text{ V}$; $f = 1\text{ MHz}$	–	13	–	pF
C_{os}	output capacitance	$V_{GS} = 0$; $V_{DS} = 26\text{ V}$; $f = 1\text{ MHz}$	–	11	–	pF
C_{rs}	feedback capacitance	$V_{GS} = 0$; $V_{DS} = 26\text{ V}$; $f = 1\text{ MHz}$	–	0.5	–	pF

UHF power LDMOS transistor

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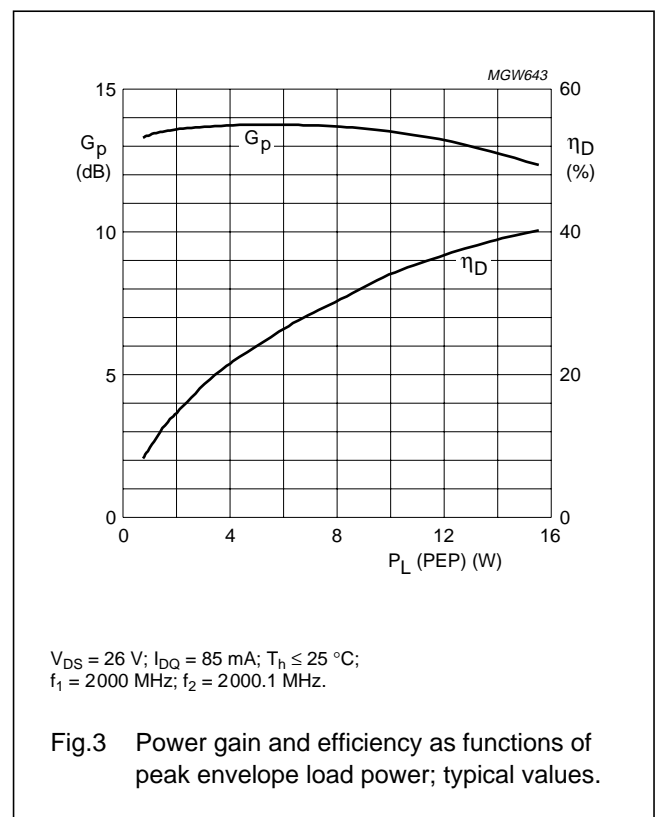
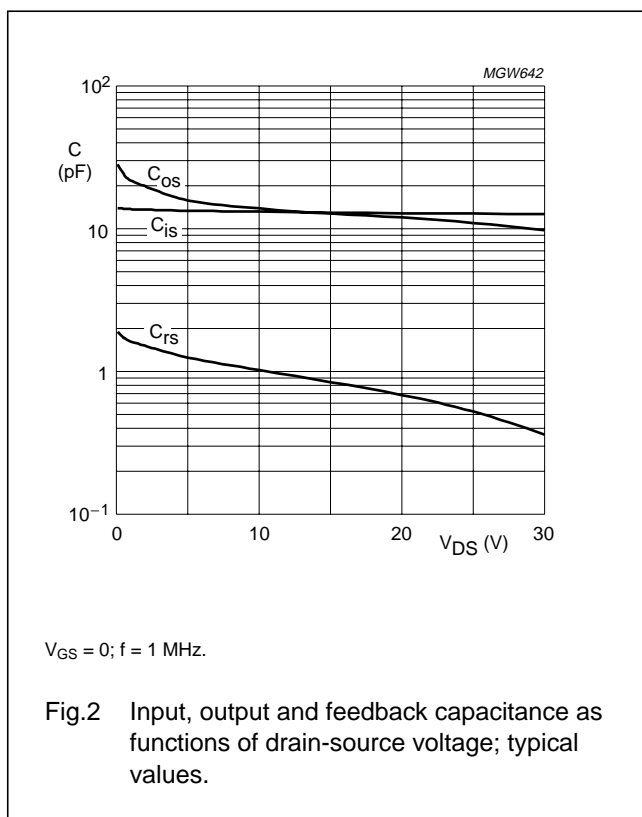
APPLICATION INFORMATION 2.2 GHz

RF performance in a common source class-AB circuit. $T_h = 25\text{ }^\circ\text{C}$; $R_{th\text{ mb-h}} = 0.4\text{ K/W}$; unless otherwise specified.

MODE OF OPERATION	f (MHz)	V _{DS} (V)	I _{DQ} (mA)	P _L (W)	G _p (dB)	η _D (%)	d _{im} (dBc)
CW, class-AB (2-tone)	f ₁ = 2200; f ₂ = 2200.1	26	85	10 (PEP)	>11	>30	≤-26

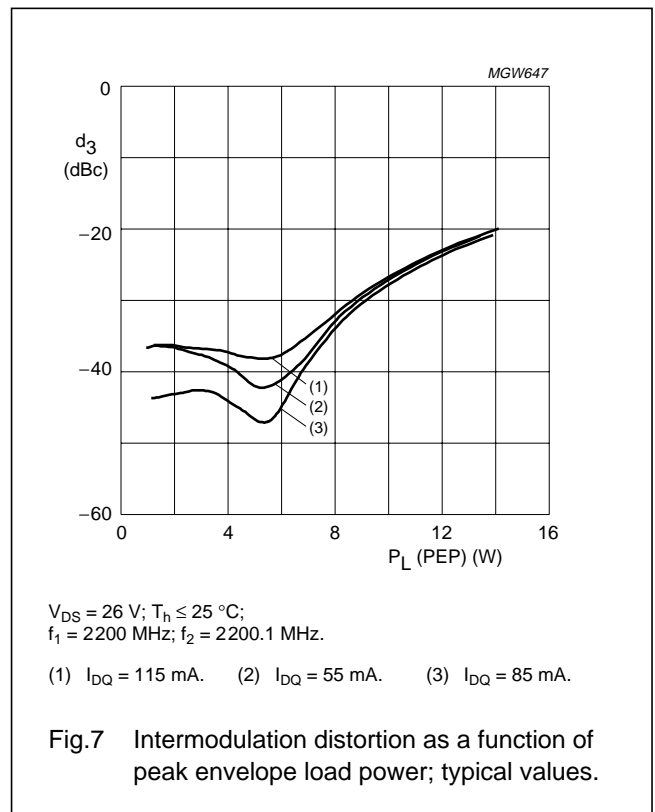
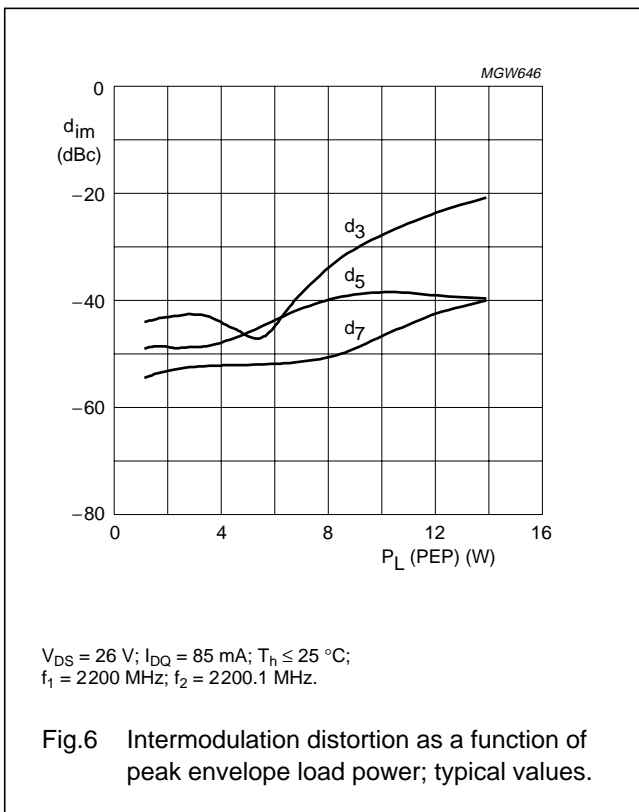
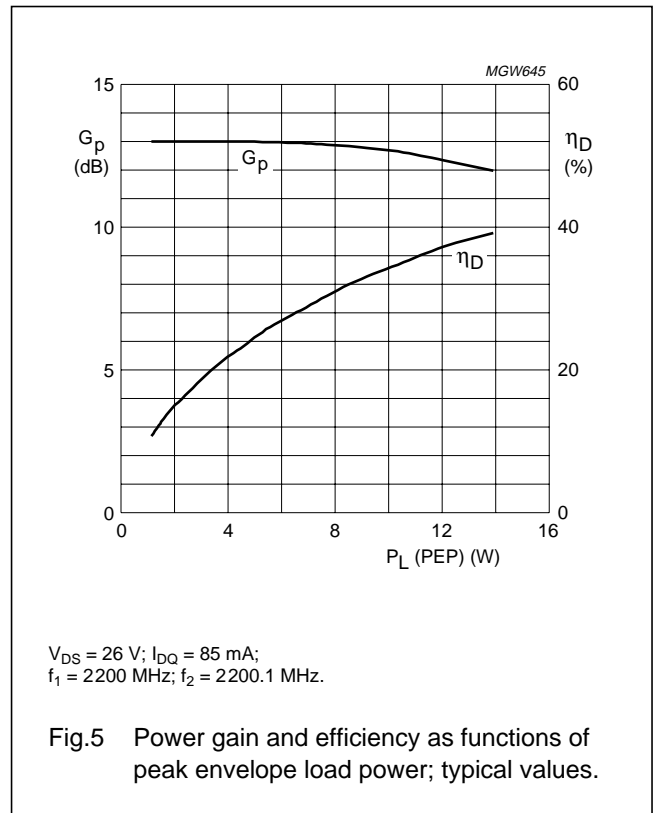
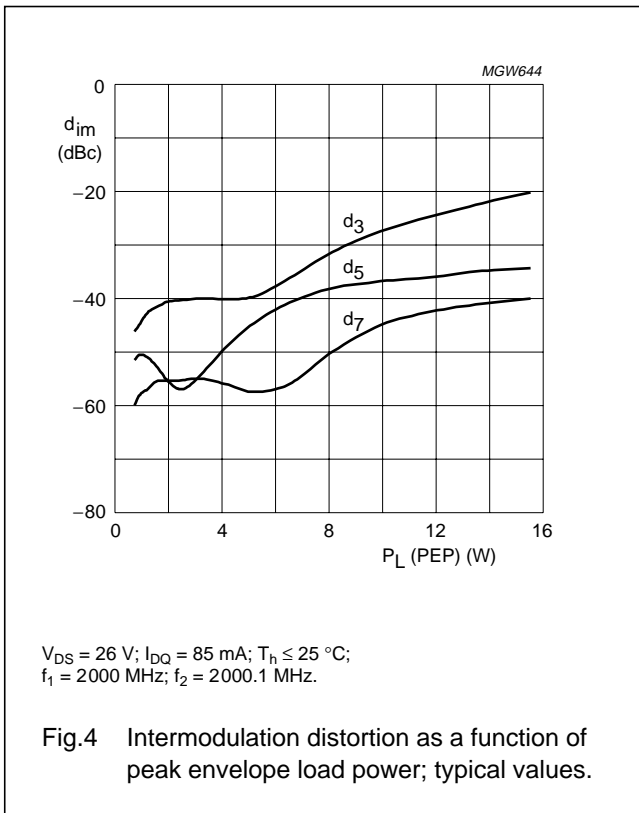
Ruggedness in class-AB operation

The BLF1822-10 is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 26 V; f = 2200 MHz at rated load power.



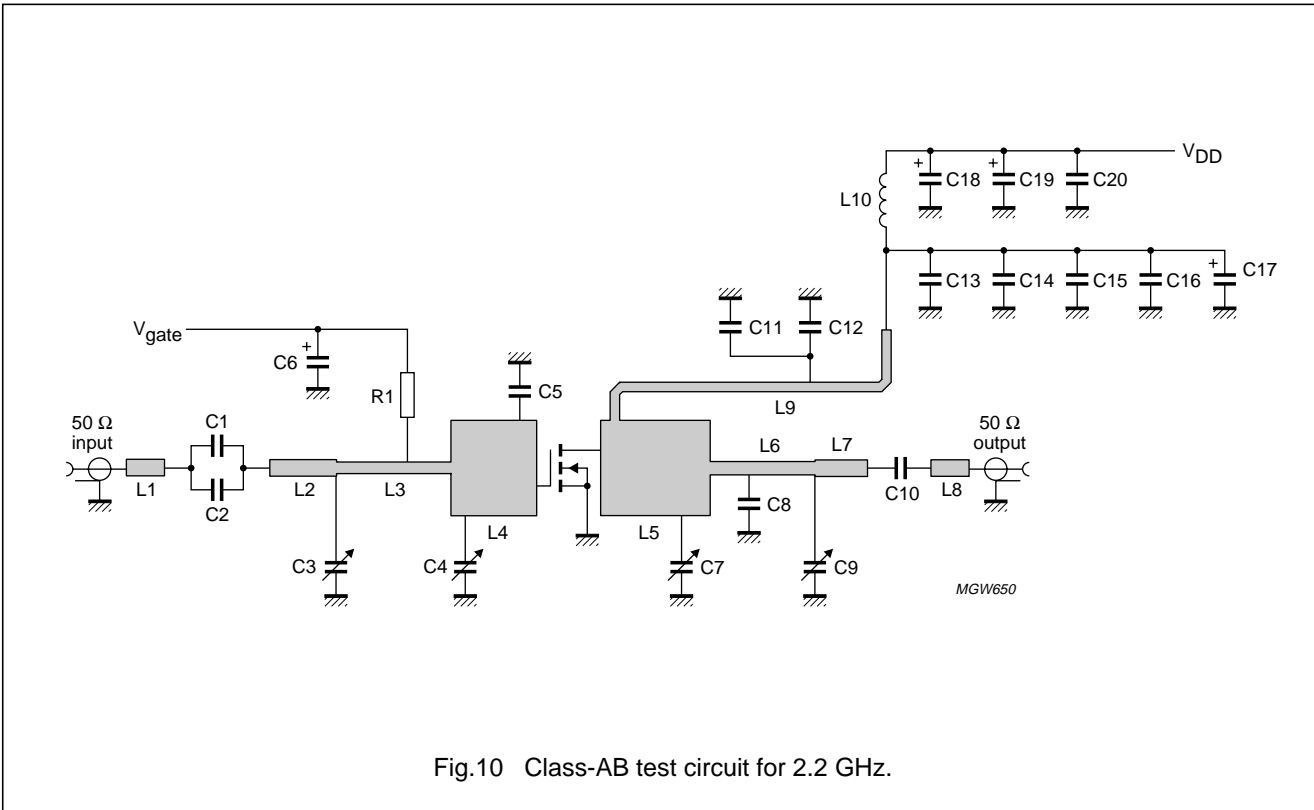
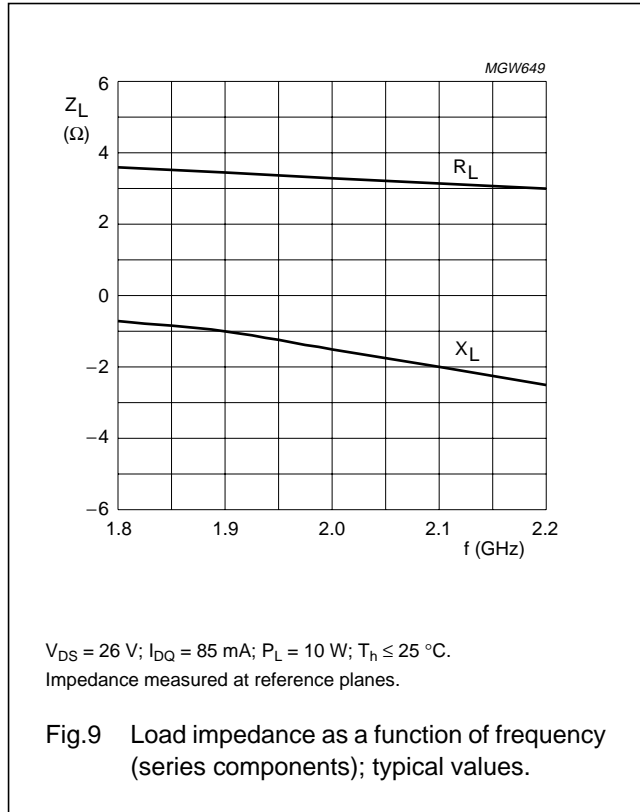
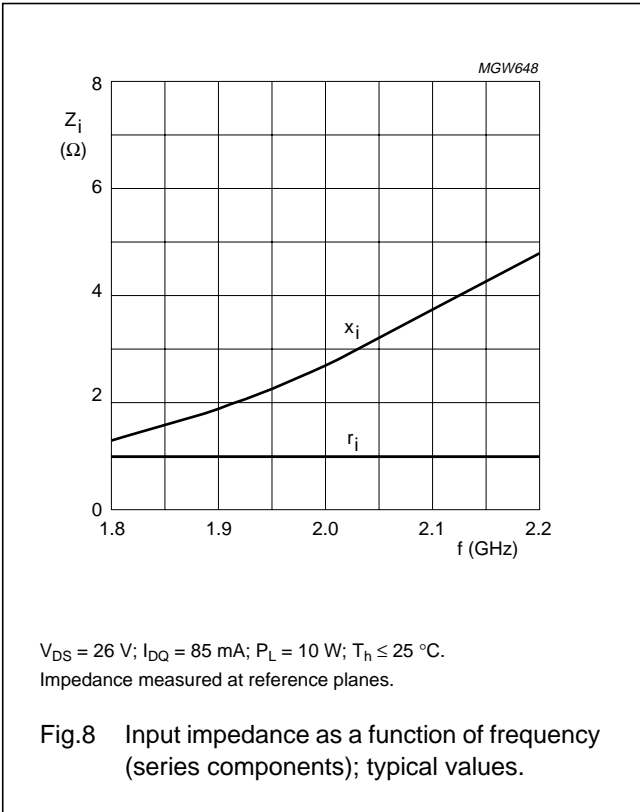
UHF power LDMOS transistor

BLF1822-10



UHF power LDMOS transistor

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UHF power LDMOS transistor

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List of components (see Figs 10 and 11)

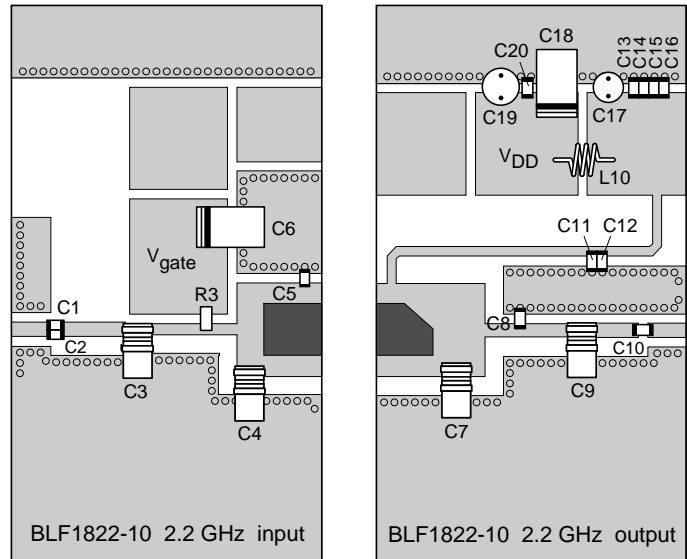
COMPONENT	DESCRIPTION	VALUE	DIMENSIONS	CATALOGUE NO.
C1, C2, C10, C11	multilayer ceramic chip capacitor; note 1	6.8 pF		
C3, C4, C7, C9	Tekelec variable capacitor; type 37271	0.6 to 4.5 pF		
C5	multilayer ceramic chip capacitor; note 1	2.4 pF		
C6, C18	tantalum SMD capacitor	10 μ F; 35 V		
C8	multilayer ceramic chip capacitor; note 1	1.5 pF		
C12, C20	multilayer ceramic chip capacitor; note 2	1 nF		
C13	multilayer ceramic chip capacitor; note 1	10 pF		
C14	multilayer ceramic chip capacitor; note 1	51 pF		
C15	multilayer ceramic chip capacitor; note 1	120 pF		
C16	multilayer ceramic chip capacitor	100 nF		2222 581 16641
C17	electrolytic capacitor	47 μ F; 35 V		2222 036 90094
C19	electrolytic capacitor	100 μ F; 63 V		2222 037 58101
L1, L8	stripline; note 3	50 Ω	4 \times 1.5 mm	
L2	stripline; note 3	50 Ω	7 \times 1.5 mm	
L3	stripline; note 3	58.1 Ω	12 \times 1.2 mm	
L4	stripline; note 3	11.3 Ω	9 \times 10 mm	
L5	stripline; note 3	11.3 Ω	11.5 \times 10 mm	
L6	stripline; note 3	52.8 Ω	11 \times 1.4 mm	
L7	stripline; note 3	50 Ω	5.5 \times 1.5 mm	
L9	stripline; note 3	64.7 Ω	38 \times 1 mm	
L10	2 turns enamelled 0.5 mm copper wire		int. dia. = 3 mm; length = 3 mm	
R1	metal film resistor	390 Ω ; 0.6 W		2322 156 11009

Notes

1. American Technical Ceramics type 100A or capacitor of same quality.
2. American Technical Ceramics type 100B or capacitor of same quality.
3. The striplines are on a double copper-clad printed-circuit board with Rogers 5880 dielectric ($\epsilon_r = 2.2$); thickness 0.51 mm.

UHF power LDMOS transistor

BLF1822-10



Dimensions in mm.

The components are situated on one side of the copper-clad printed-circuit board with Teflon dielectric ($\epsilon_r = 2.2$), thickness 0.51 mm. The other side is unetched and serves as a ground plane.

Fig.11 Component layout for 2.2 GHz class-AB test circuit.

UHF power LDMOS transistor

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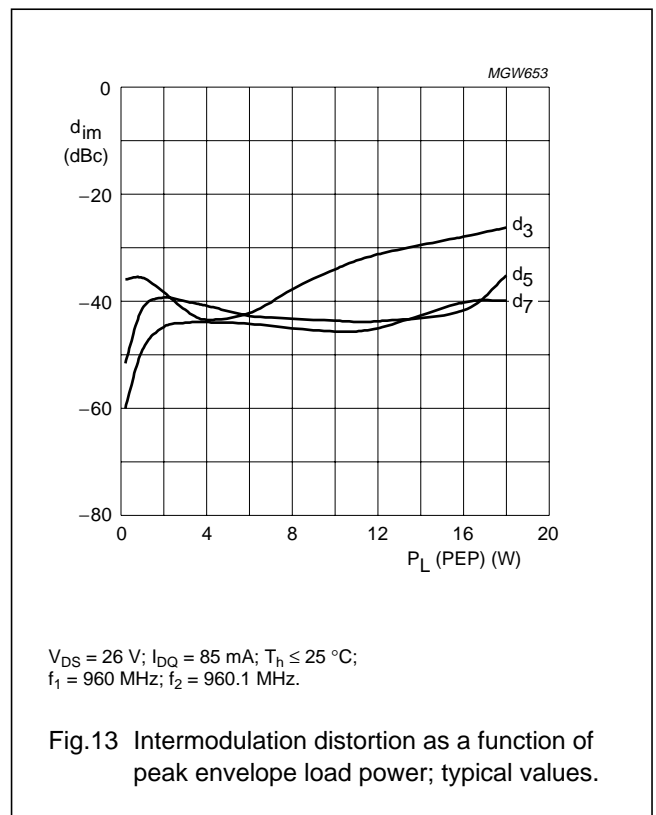
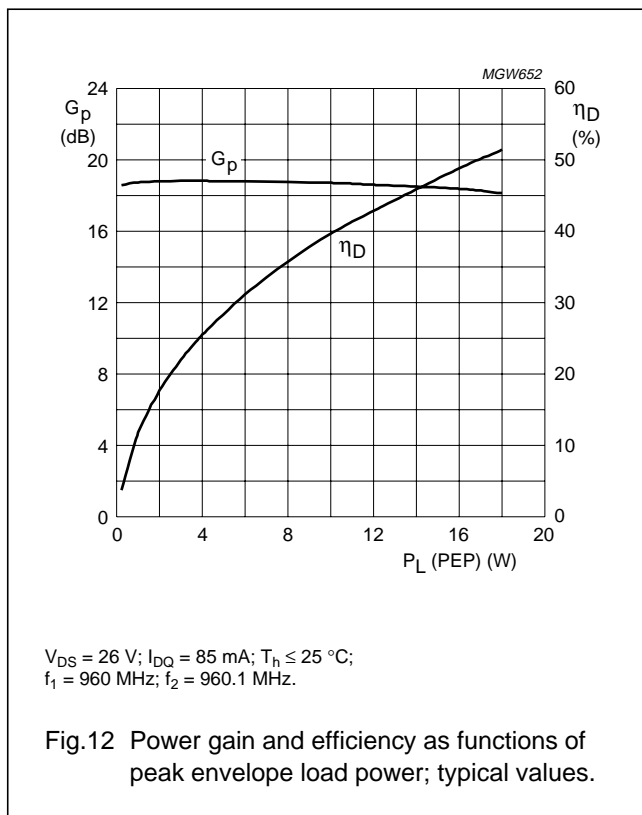
APPLICATION INFORMATION 960 MHz

RF performance in a common source class-AB circuit. $T_h = 25\text{ }^\circ\text{C}$; $R_{th\ mb-h} = 0.4\text{ K/W}$; unless otherwise specified.

MODE OF OPERATION	f (MHz)	V _{DS} (V)	I _{DQ} (mA)	P _L (W)	G _p (dB)	η _D (%)	d _{im} (dBc)
CW, class-AB (2-tone)	f ₁ = 960; f ₂ = 960.1	26	85	10 (PEP)	typ. 18.5	typ. 39	typ. -33

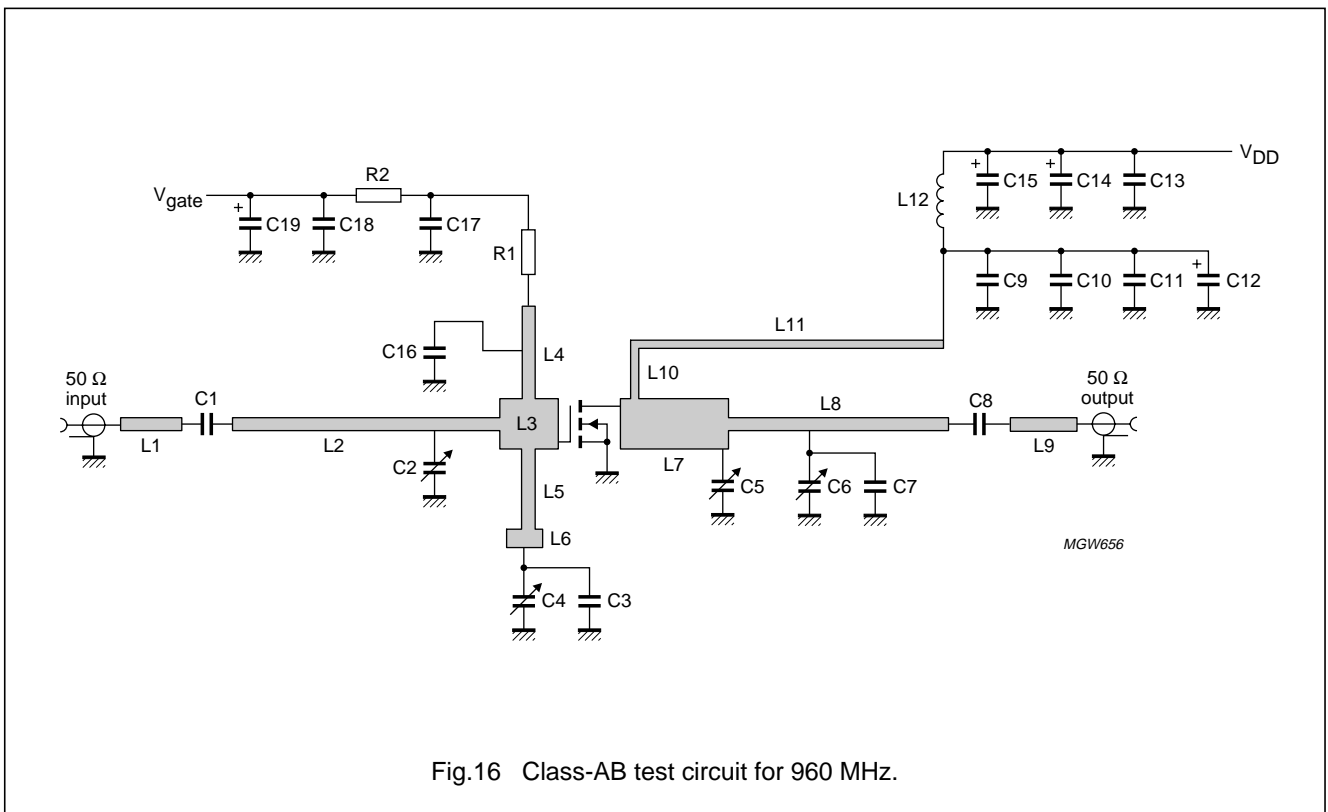
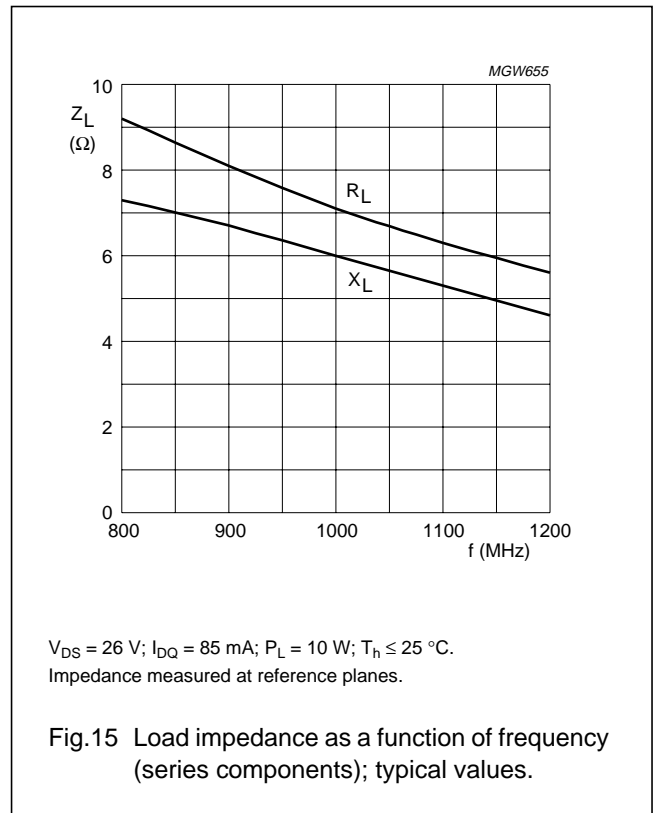
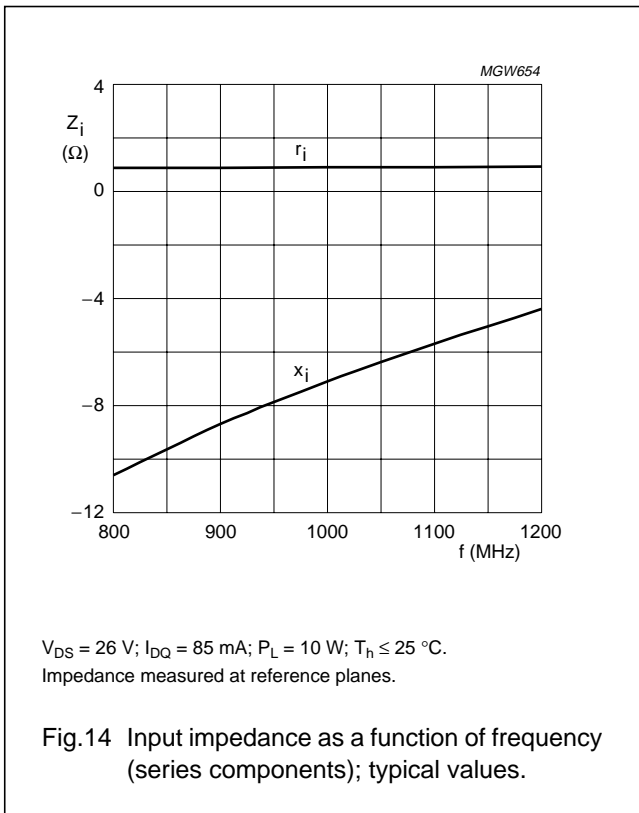
Ruggedness in class-AB operation

The BLF1822-10 is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 26 V; f = 960 MHz at rated load power.



UHF power LDMOS transistor

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UHF power LDMOS transistor

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List of components (see Figs 16 and 17)

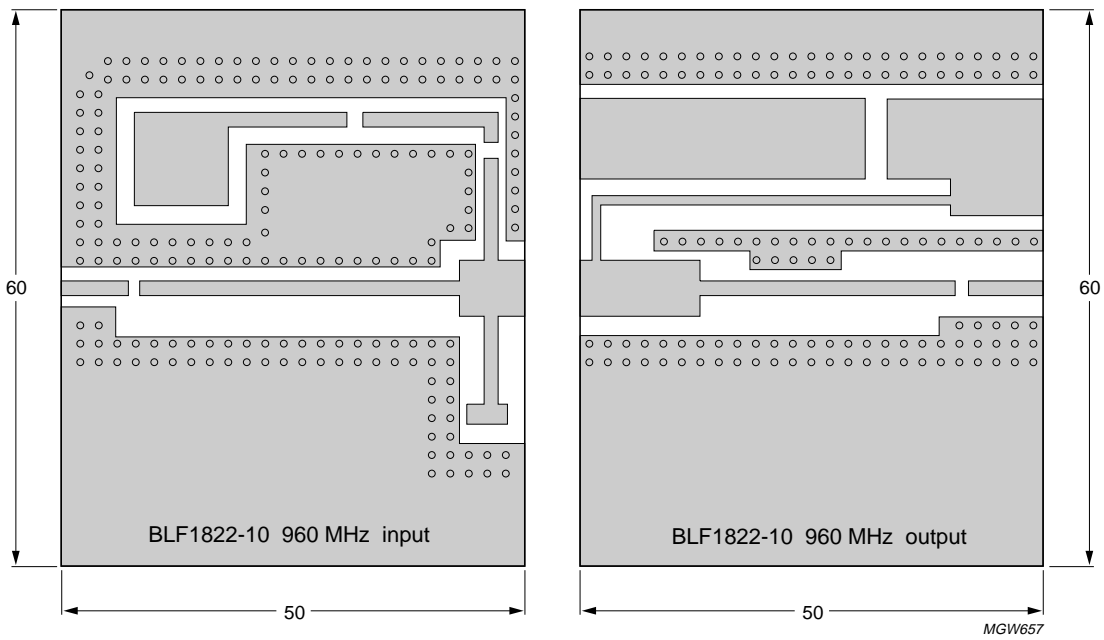
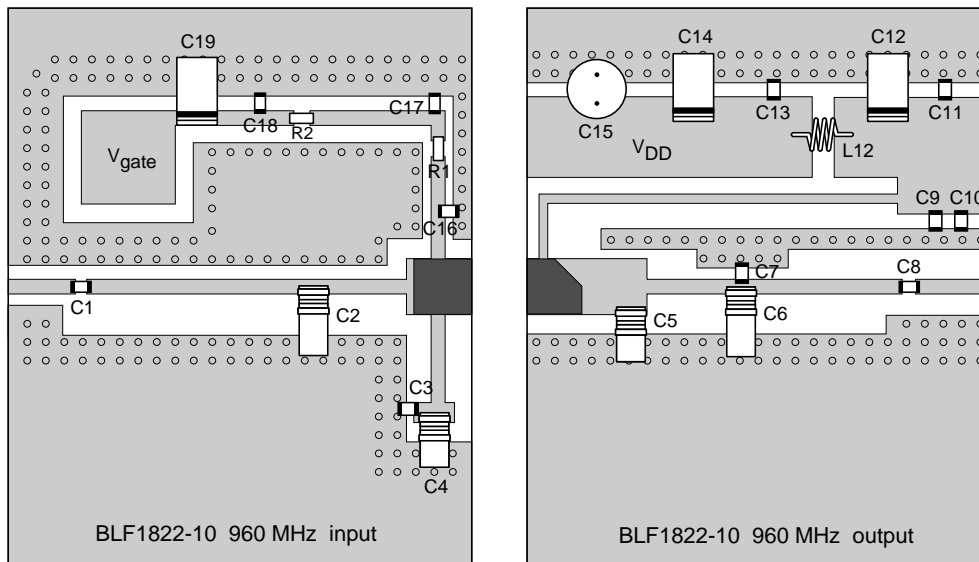
COMPONENT	DESCRIPTION	VALUE	DIMENSIONS	CATALOGUE NO.
C1	multilayer ceramic chip capacitor; note 1	82 pF		
C2, C6	Tekelec variable capacitor; type 27291	0.8 to 8 pF		
C3	multilayer ceramic chip capacitor; note 1	0.3 pF		
C4, C5	Tekelec variable capacitor; type 27271	0.6 to 4.5 pF		
C7	multilayer ceramic chip capacitor; note 1	2.1 pF		
C8	multilayer ceramic chip capacitor; note 2	56 pF		
C19, C14, C19	multilayer ceramic chip capacitor	100 pF	size 0805	
C10, C17	multilayer ceramic chip capacitor	1 nF	size 0805	
C12, C14, C19	tantalum SMD capacitor	6.8 μ F		
C13	multilayer ceramic chip capacitor	100 nF		2222 581 16641
C15	electrolytic capacitor	100 μ F; 63 V		2222 037 58101
C16	multilayer ceramic chip capacitor; note 1	68 pF		
L1	stripline; note 3	50 Ω	7.5 \times 1.57 mm	
L2	stripline; note 3	50 Ω	34.5 \times 1.57 mm	
L3	stripline; note 3	19.2 Ω	7 \times 6 mm	
L4	stripline; note 3	50 Ω	11 \times 1.57 mm	
L5	stripline; note 3	50 Ω	9.5 \times 1.57 mm	
L6	stripline; note 3	24.5 Ω	2.2 \times 4.4 mm	
L7	stripline; note 3	19.2 Ω	13 \times 6 mm	
L8	stripline; note 3	50 Ω	27.5 \times 1.57 mm	
L9	stripline; note 3	50 Ω	8 \times 1.57 mm	
L10	stripline; note 2	64.4 Ω	6.4 \times 1 mm	
L11	stripline; note 3	64.4 Ω	38 \times 1 mm	
L12	3 turns enamelled 0.5 mm copper wire		int. dia. = 4 mm length = 5 mm	
R1	resistor	51 Ω , 0.25 W	size 1206	
R2	resistor	1 k Ω , 0.25 W	size 1206	

Notes

1. American Technical Ceramics type 500A or capacitor of same quality.
2. American Technical Ceramics type 100B or capacitor of same quality.
3. The striplines are on a double copper-clad printed-circuit board with Rogers 4350 dielectric ($\epsilon_r = 3.81$); thickness 0.76 mm.

UHF power LDMOS transistor

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Dimensions in mm.

The components are situated on one side of the copper-clad printed-circuit board with Rogers 4350 dielectric ($\epsilon_r = 3.81$), thickness 0.76 mm. The other side is unetched and serves as a ground plane.

Fig.17 Component layout for 960 MHz class-AB test circuit.

MGW657

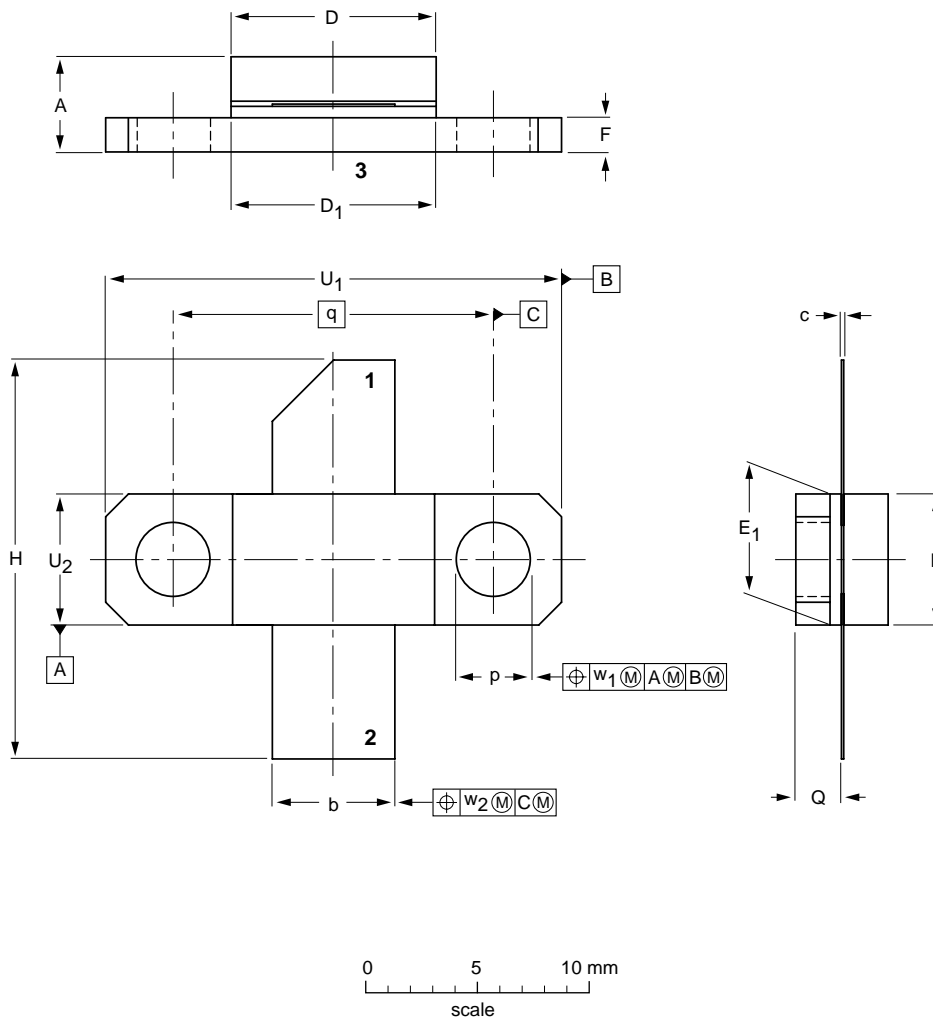
UHF power LDMOS transistor

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PACKAGE OUTLINE

Flanged LDMOST ceramic package; 2 mounting holes; 2 leads

SOT467C



DIMENSIONS (millimetre dimensions are derived from the original inch dimensions)

UNIT	A	b	c	D	D ₁	E	E ₁	F	H	p	Q	q	U ₁	U ₂	w ₁	w ₂
mm	4.67 3.94	5.59 5.33	0.15 0.10	9.25 9.04	9.27 9.02	5.92 5.77	5.97 5.72	1.65 1.40	18.54 17.02	3.43 3.18	2.21 1.96	14.27	20.45 20.19	5.97 5.72	0.25	0.51
inch	0.184 0.155	0.220 0.210	0.006 0.004	0.364 0.356	0.365 0.355	0.233 0.227	0.235 0.225	0.065 0.055	0.73 0.67	0.135 0.125	0.087 0.077	0.562	0.805 0.795	0.235 0.225	0.010	0.020

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT467C						99-12-06 99-12-28

UHF power LDMOS transistor

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DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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NOTES

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